

RE22- PANDA MVD

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on behalf of the PANDA MVD group



Overview

Request: test of silicon device prototypes for the Micro Vertex Detector of PANDA (RE22) experiment.

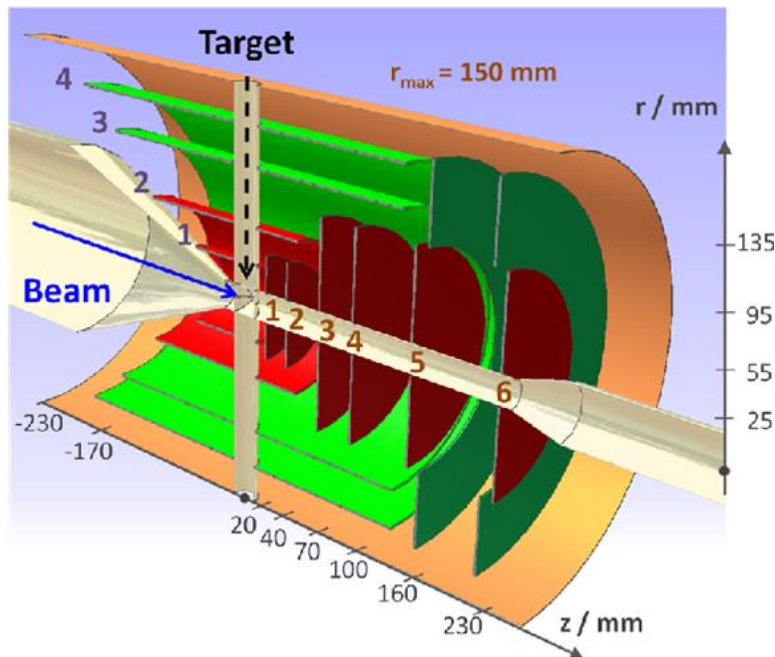
- Available Prototypes
- Setup: reduction of the space request
- Beam time: scheduled too early in July

The Micro Vertex Detector

It must combine good space resolution with accurate time-tagging

Main functions

- Primary vertex reconstruction
- Identification of the secondary vertices ($c\tau$ of some hundreds of μm)
- Improvement in momentum resolution
- Support PID of low momentum particles by energy loss measurement



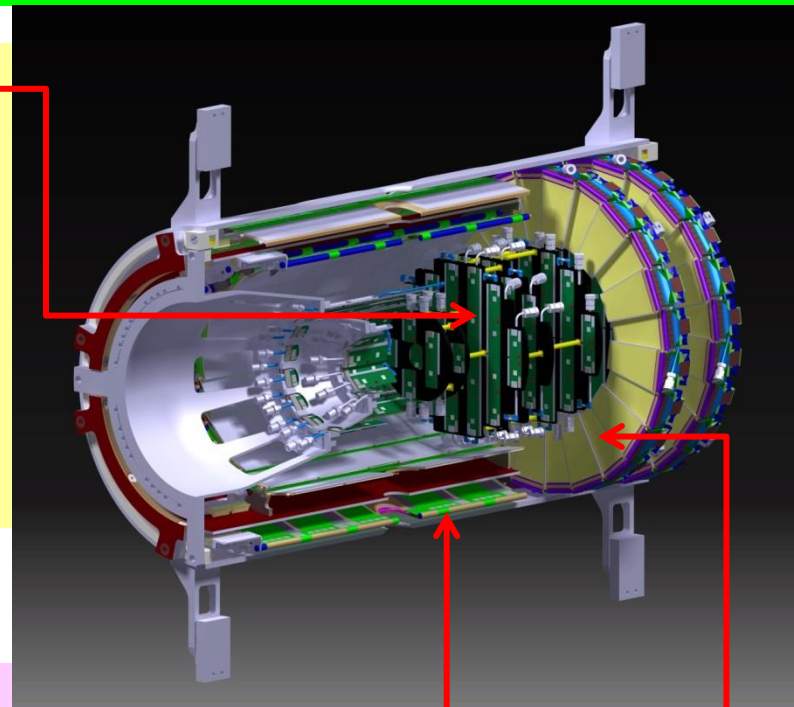
- Good spatial resolution (some tens of μm in $\rho\phi$, better than $100 \mu\text{m}$ along z)
- Time resolution $< 10 \text{ ns}$
- **Continuous readout** at $\sim 10^7$ interactions / s (**clock signal @160 MHz**)
- Limited material budget $X/X_0 \leq 1 \% / \text{layer}$
- Radiation tolerance $< 10^{14} \text{ n}_{1 \text{ MeV eq}} \text{ cm}^{-2}$
- Provide at least four hits per track
- Energy loss measurement
- Room temperature operation
- Routing and services only in the backward region

10.3 M (pixel channels) – active area: 0.106 m^2
162 k (strip channels) – active area: 0.494 m^2

Silicon devices

Hybrid epitaxial silicon pixel:

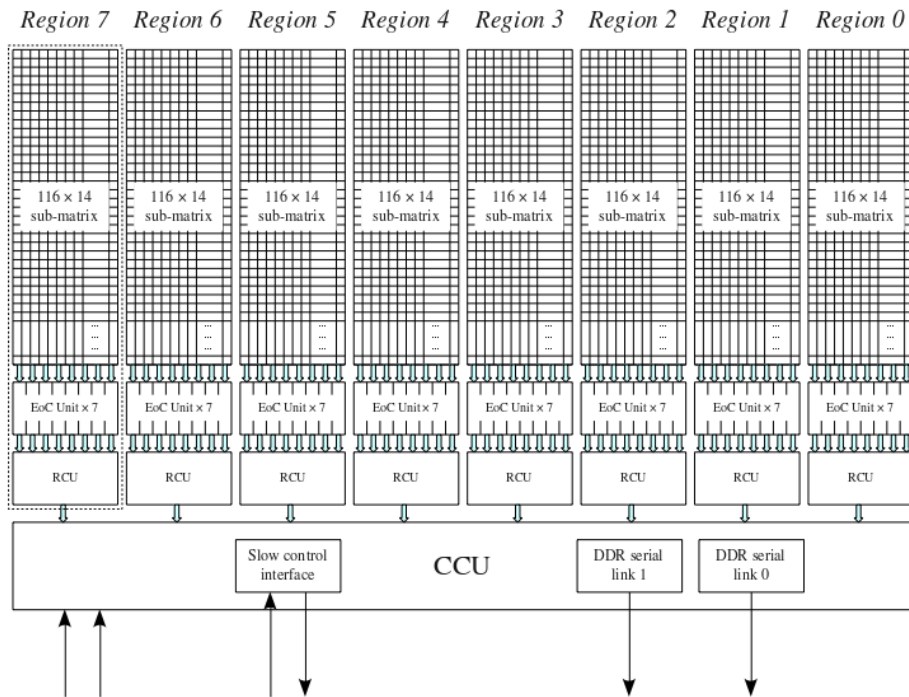
- ✓ **Sensor** made of Epitaxial Silicon material
 - $\rho_{\text{epi}} \sim \text{k}\Omega\cdot\text{cm}$
 - $\rho_{\text{Cz}} \sim 20\text{-}50 \text{ m}\Omega\cdot\text{cm}$
- ✓ **Pixel cell size:** $100\mu\text{m} \times 100\mu\text{m} \times 100\mu\text{m}$
- ✓ **ASIC** developed in 130 nm CMOS technology (ToPix)
 - Triggerless
 - dE/dx using Time over Threshold technique



Double sided silicon micro strips:

- ✓ Rectangular (512 x 896 strips) and squared (512 x 512 strips) **sensors**;
stereo angle: 90° , strip pitch: $67.5 \mu\text{m}$, $285 \mu\text{m}$ thickness
- ✓ Trapezoidal (768 x 768 strips) **sensors**;
stereo angle: 15° , pitch: $45 \mu\text{m}$, $285 \mu\text{m}$ thickness
- ✓ **ASIC** developed in 110 nm CMOS technology (PASTA)
 - Triggerless
 - ToT technique for dE/dx measurement

ToPix



- Columns divided in 8 regions with 7 double columns each
- FIFO in the end of column and region control
- Output bandwidth: 2 x 320 Mb/s
- Supply voltage: 1.2 V

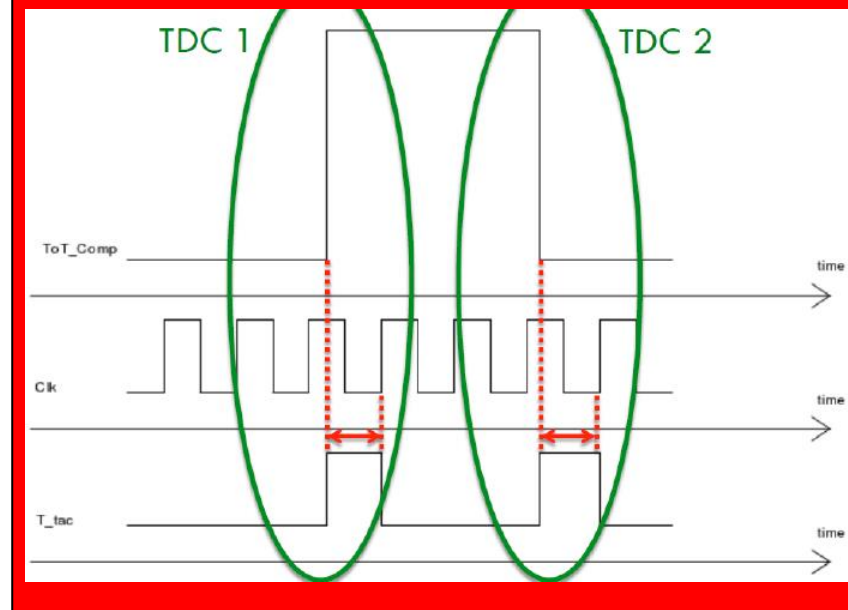
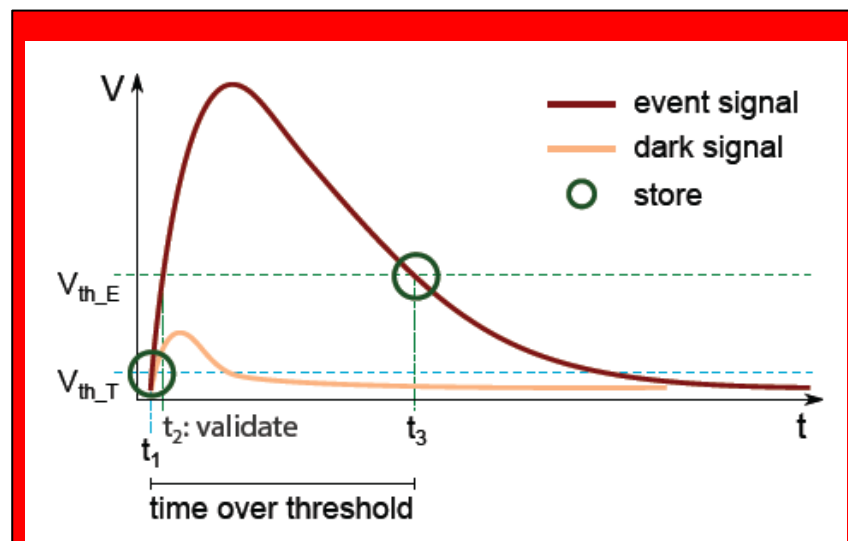
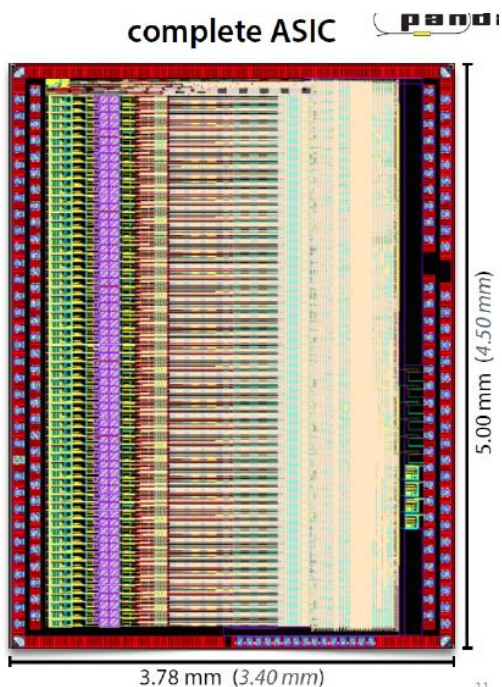
- Pixel matrix: 110 x 116
- Size (to be optimized): 11.2 mm x 14.8 mm
- dE/dx measurement: ToT, 12 bits dynamic range
- Maximum input charge: 50 fC
- Detector type: n and p
- Noise floor: < 200 electrons
- Input clock frequency: 160 MHz
- Time resolution: ~ 6 ns
- Power consumption: ≤ 0.8 W/cm²
- Maximum event rate/cm²: $\sim 6.1 \times 10^6$
- Data rate per chip: up to ~ 450 Mb/s

PASTA

First prototype under submission:

- 64 channel (full size), 3.8 mm x 4.5 mm
- Input capacitance/charge: \rightarrow 25 fF / 40 fC
- Dynamic range: 8 bit
- Power consumption: $<$ 4 mW/ch
- Noise $<$ 1500 e $^-$
- Time bin width \sim 100 ps
- Channel pitch: 60 μ m

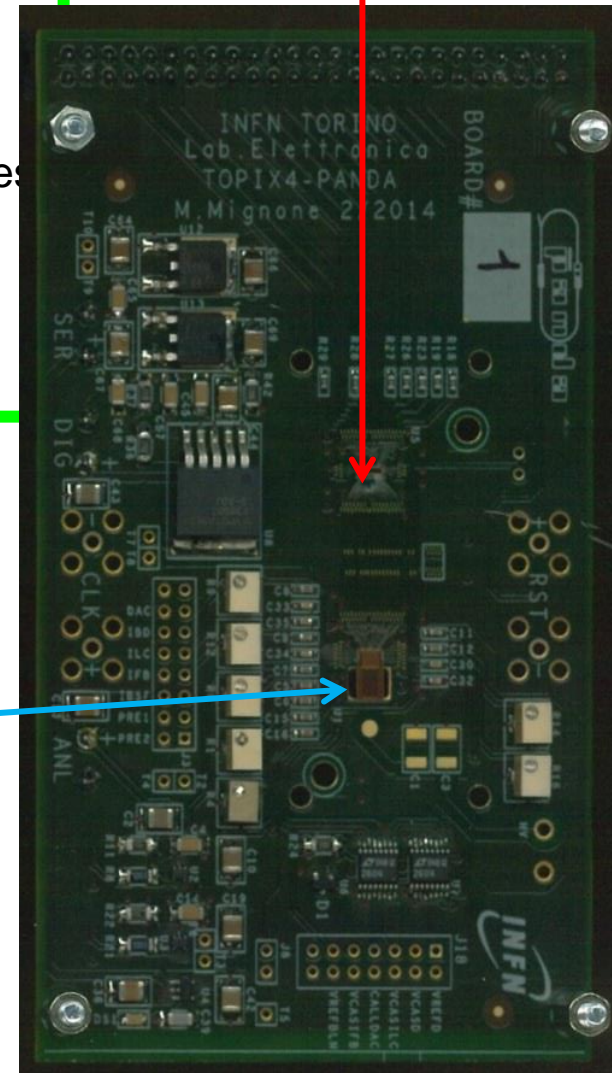
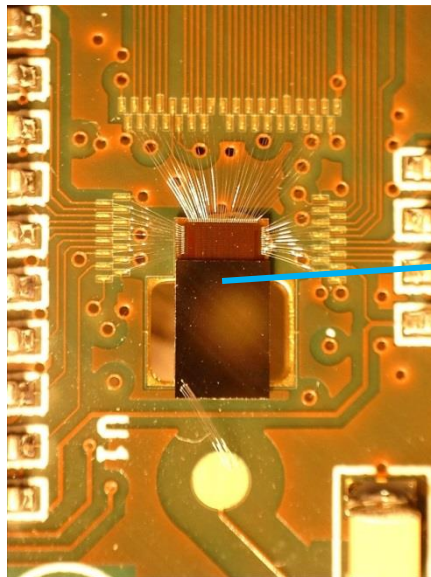
Development of TofPet Project



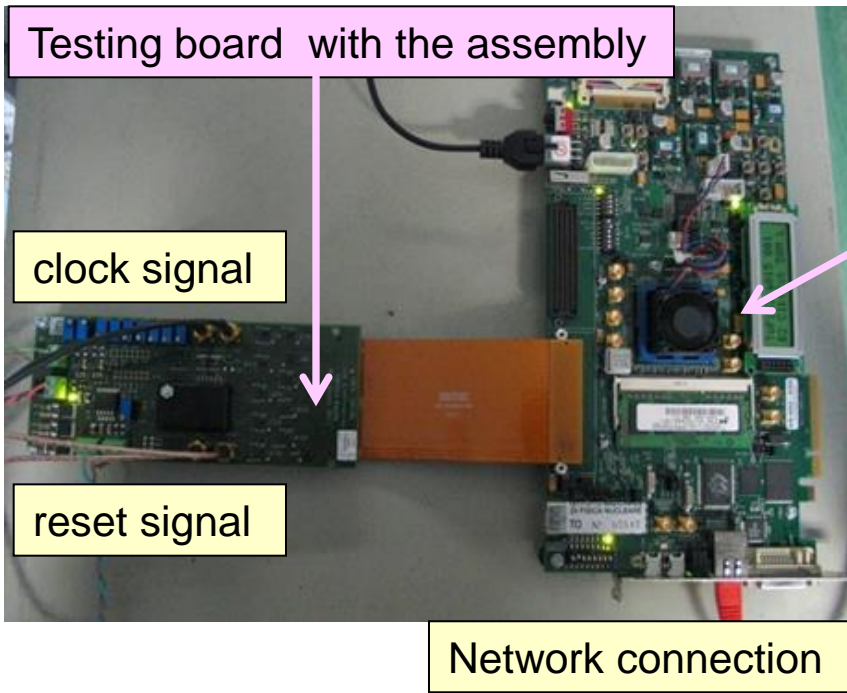
Single chip assembly based on ToPix_v4

- ASIC size: 3 mm x 6 mm
- 130 nm CMOS technology
- Input clock frequency: 160 MHz
- Pixel matrix: 640 cells (100 μ m x 100 μ m x 100 μ m), 2x2x128 and 2x2x32 columns
- Epitaxial silicon **sensor** (100 μ m thick): **3.2 mm x 2 mm**
- Hamming encoding and TMR pixel logic protection
- Leading and trailing edge registers with DICE -protected latches
- SEU protected EoC
- Serial data output (SDR and DDR)
- Frame based transmission
- GBT compatible SLVS I/O

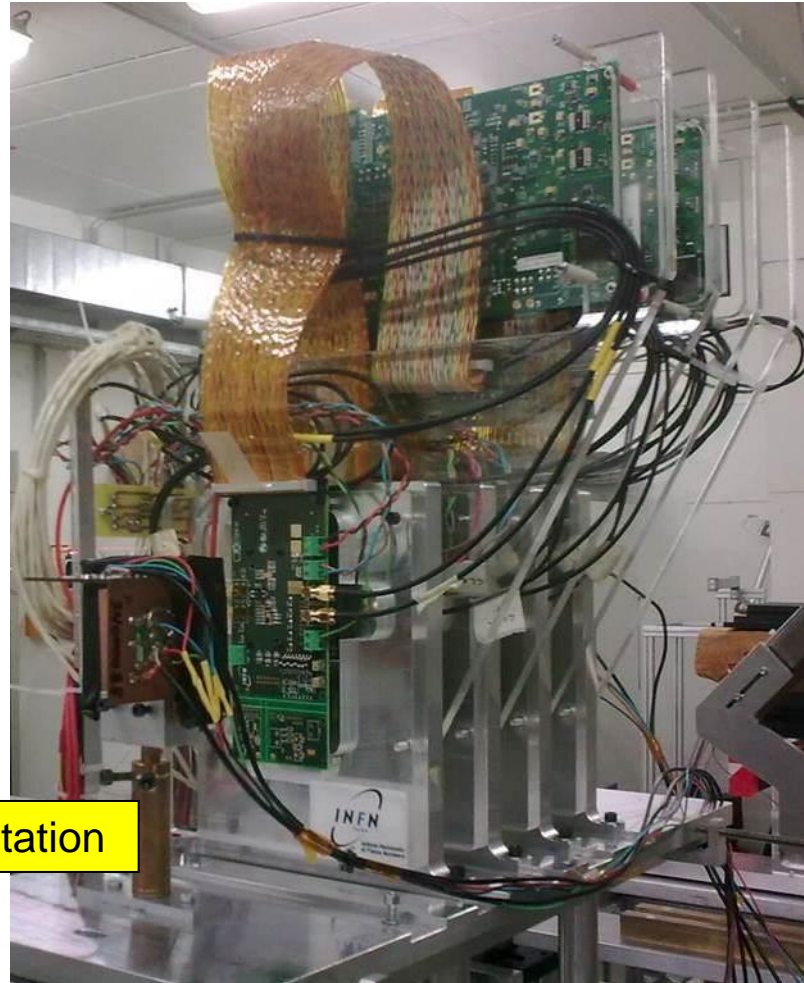
SLVS-LVDS translator



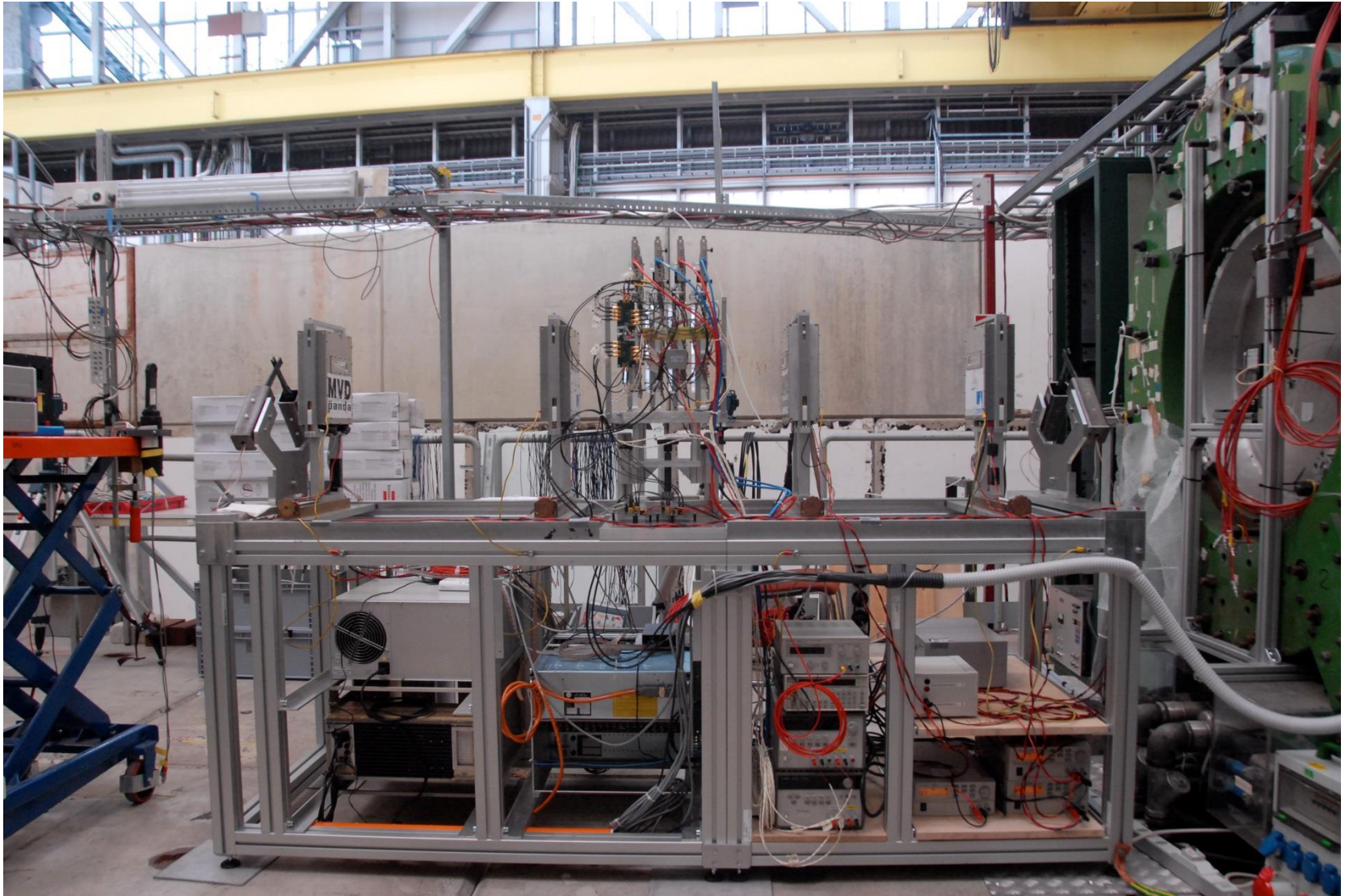
Setup



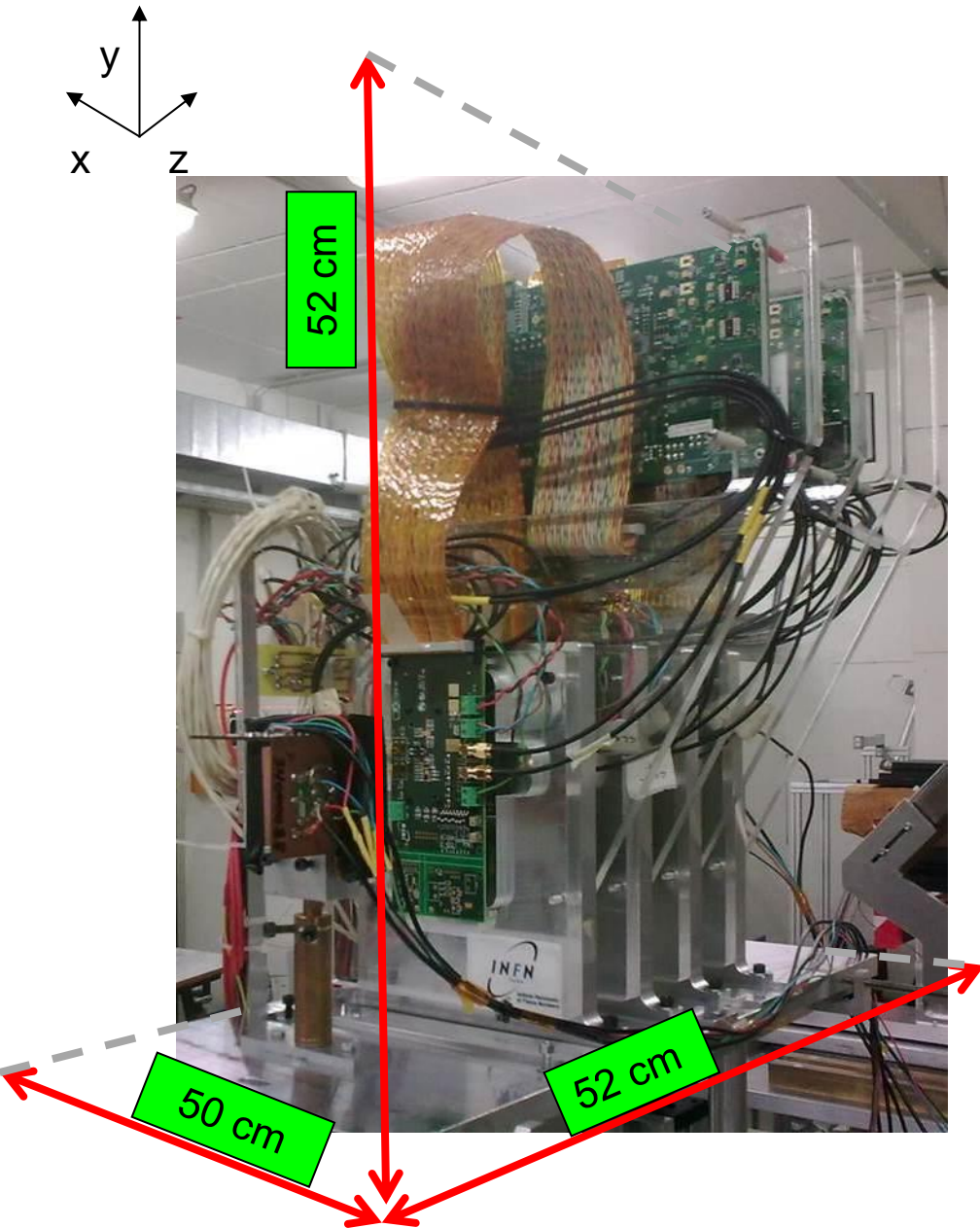
Xilinx Evaluation Board equipped with a Virtex 6 FPGA



Long table for pixel and strips



Pixel tracking station



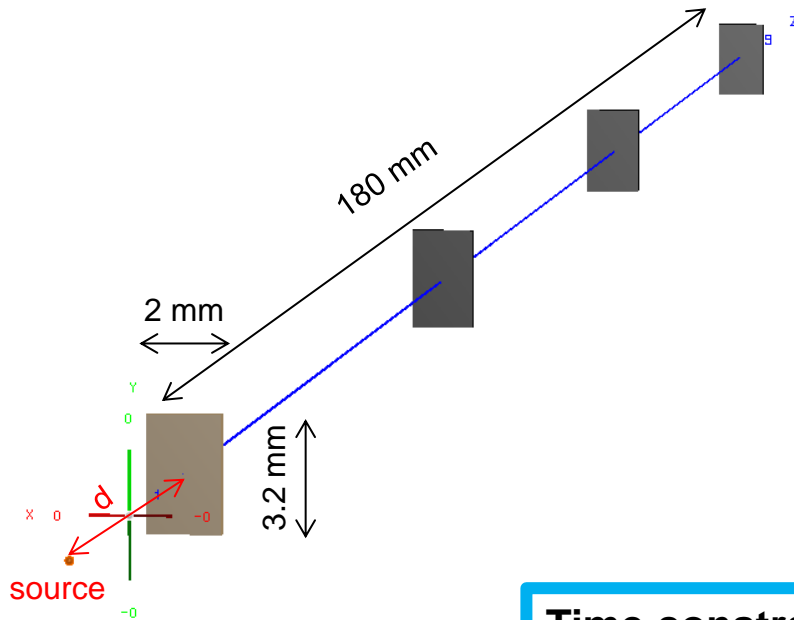
Requests to Cern:

- x-y table
- alignment support along the beam line
- Equipment to check alignment during the data taking.

- Power requirements: 220 V- 20 A
- Point to point Ethernet cables (min. 2 lines, max. length less than 30 m) between the setup and the counting room
- Space to allocate 4 power supplies and 1 crate NIM close the setup

- in the counting room , 2 workstations for daq and analysis

Beam parameter request



Requests to Cern:

- Pion beam momenta: 10 GeV/c and 100-150 GeV/c (polarity does not matter)
- (Proton beam momentum: 20 GeV/c and 100 GeV/c)
- Beam size: 3 mm x 3 mm
- @ different intensities: 10^4 , 10^5 , 10^6 , 10^7 /spill
- Spill length of ~ 10 s, interspill time of ~ 50 s
- Beam divergence:
 - Point-like source @ $d=30$ cm: $\sim 0.19^\circ$
 - @ $d=60$ cm: $\sim 0.12^\circ$
 - @ $d=100$ cm: $\sim 0.08^\circ$

Time constraints:

- Not before of the last week of July (I mean not before July 27th)
- The present schedule foresees beam already Wednesday 22nd

SPARES

D. Calvo

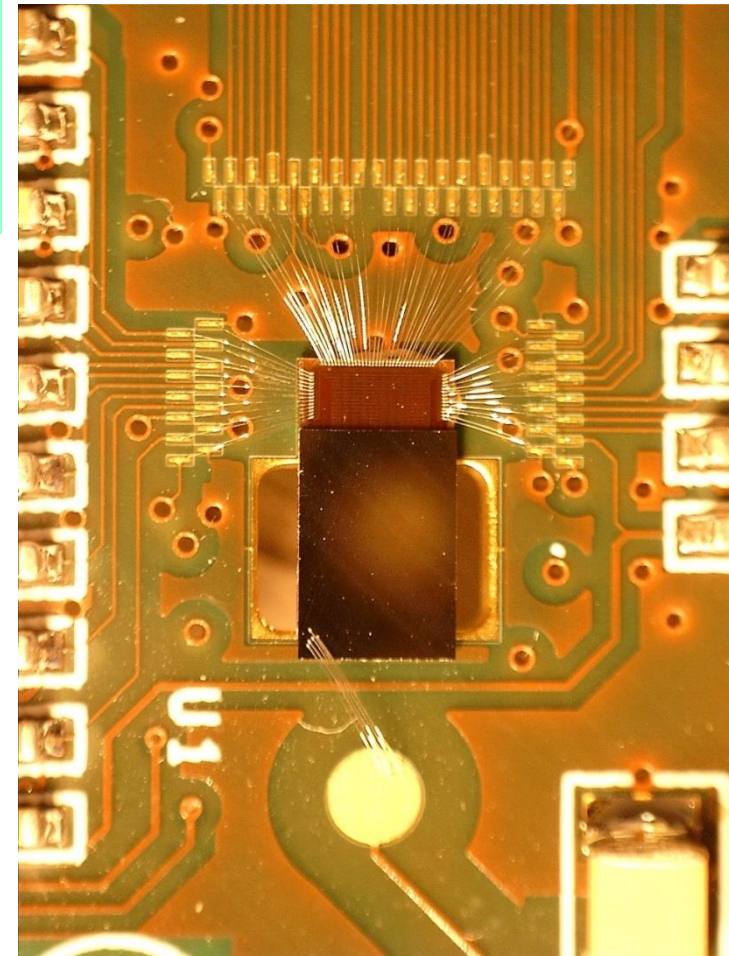
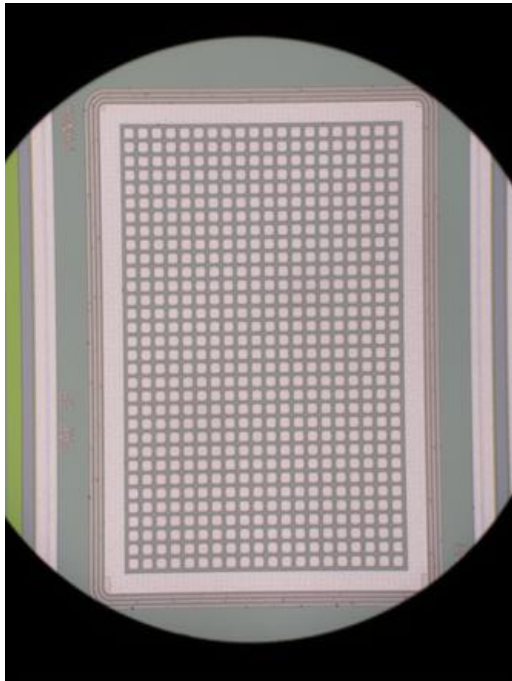


Single chip assembly

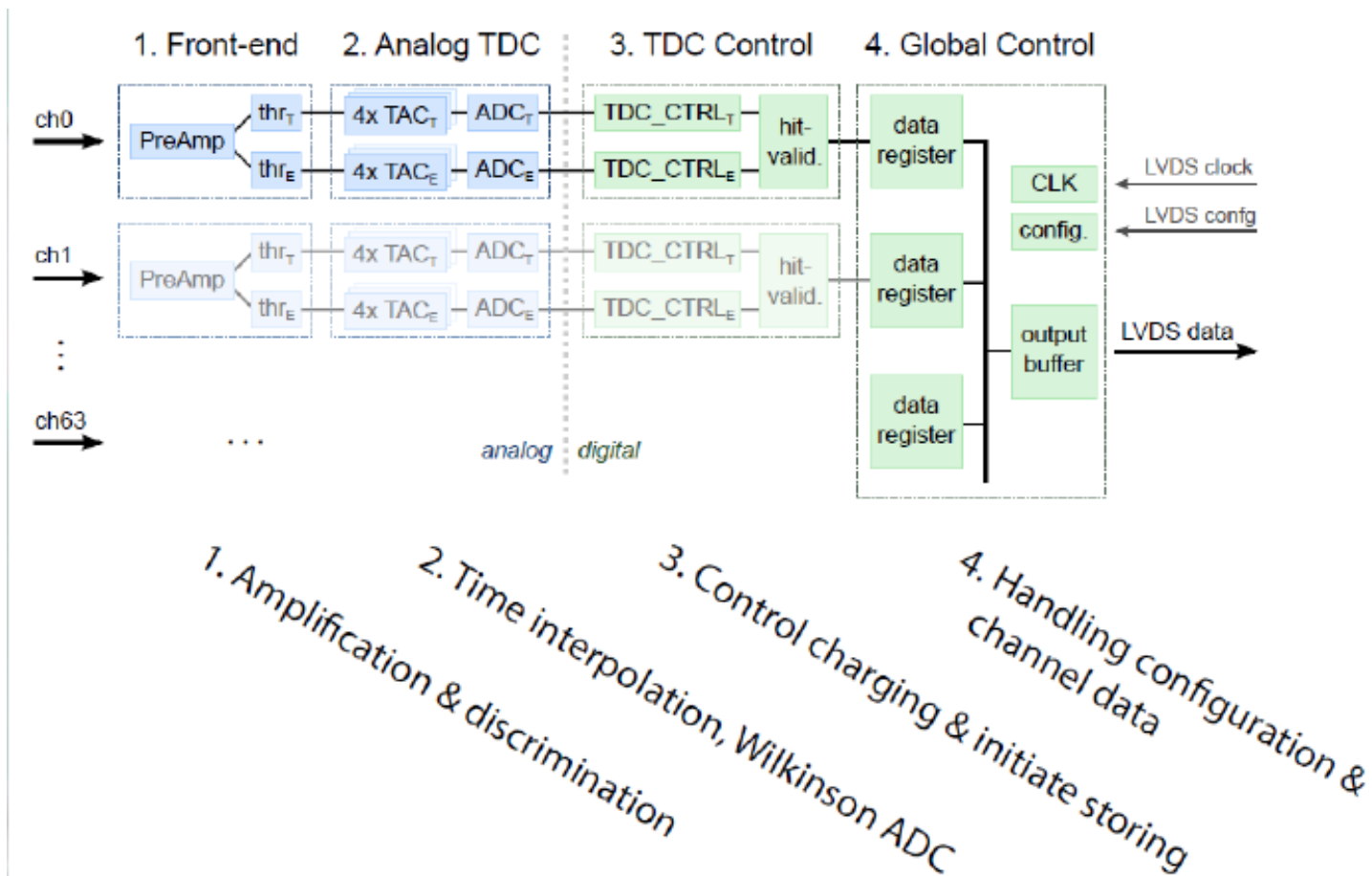
- Epitaxial silicon wafer by ITME (Varsaw)
 $\rho_{\text{epi}} \sim 1500 \Omega \cdot \text{cm}$
- Pixels @ FBK (Trento)
 $100\mu\text{m} \times 100\mu\text{m}$
- Cz thinning + Bump bonding @ IZM (Berlin)
Sn-Pb bumps
Bump bonding yield of the tested assemblies: $\sim 99.5 \%$
Thin Cz layer is the ohmic contact for the sensor biasing

20 pixels
←→

32 pixels
↑↓



PASTA architecture



ToPix4 data format

2	12	8	12	6
01	Chip address	FC	Not used	ECC
2	14	12	12	
11	Pixel address	Leading edge time	Trailing edge time	
2	16	16	6	
10	# of events	CRC	ECC	
2	38			
00	idle code (Hex 3A55AA55AA)			

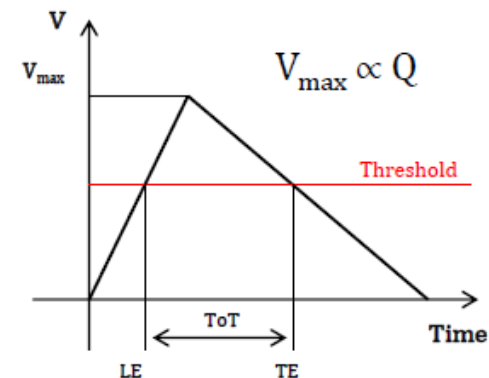
Frame header packet

Data packet

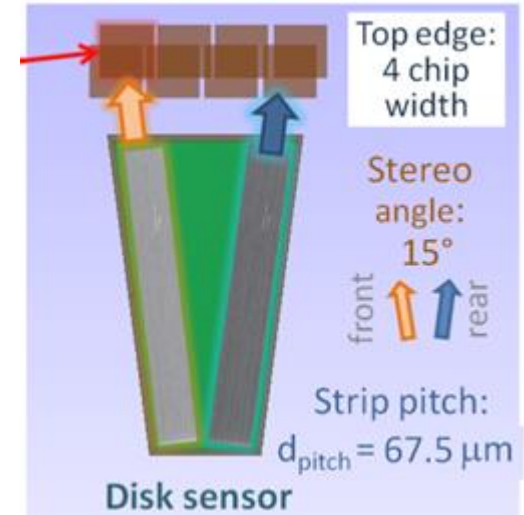
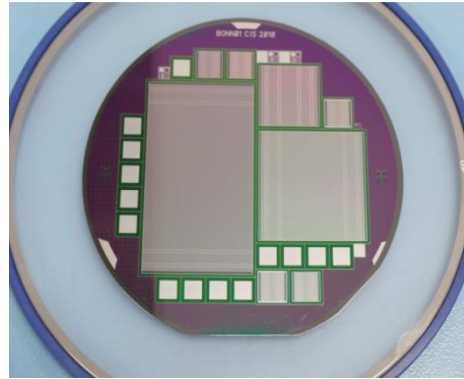
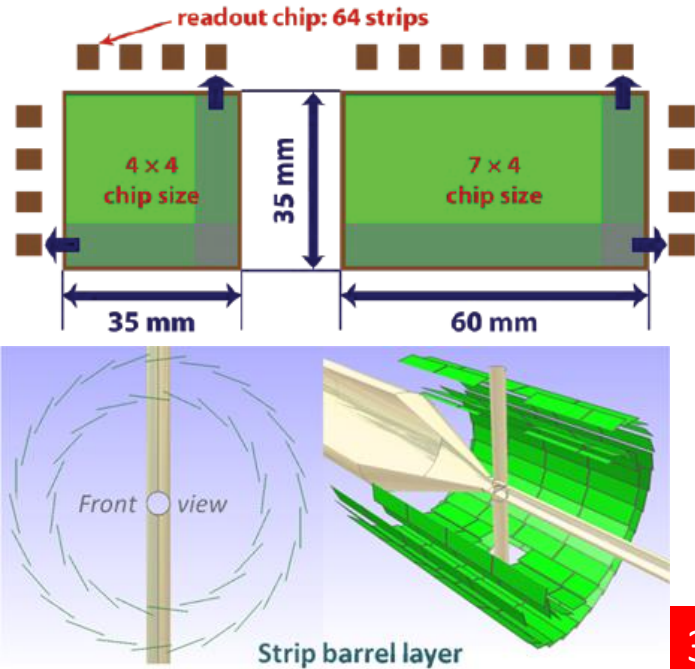
Frame trailer packet

Idle packet

Output frequency	160, 320 Mb/s
Time stamp counter frequency	160, 80 MHz
Time stamp mode	Binary, Gray
Idle packet	off, on
Analog timeout	off, on
Detector type	n-type, p-type
SLVS current control	0000 (max), 1111(off)
Driver pre-emphasis	off, on



Double-sided silicon strips



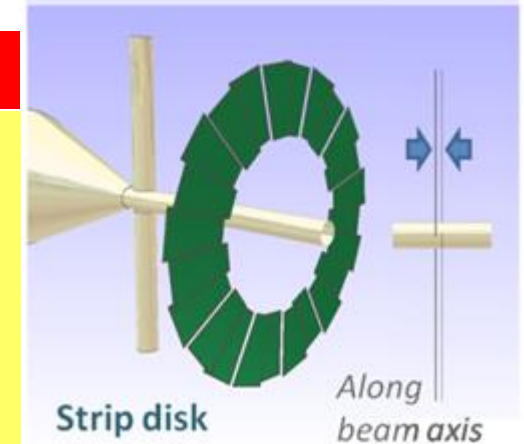
3112 readout chips / 296 sensors

Rectangular (512 x 896 strips) and squared (512 x 512 strips) **sensors**;
stereo angle: 90°, pitch: 67.5 μm

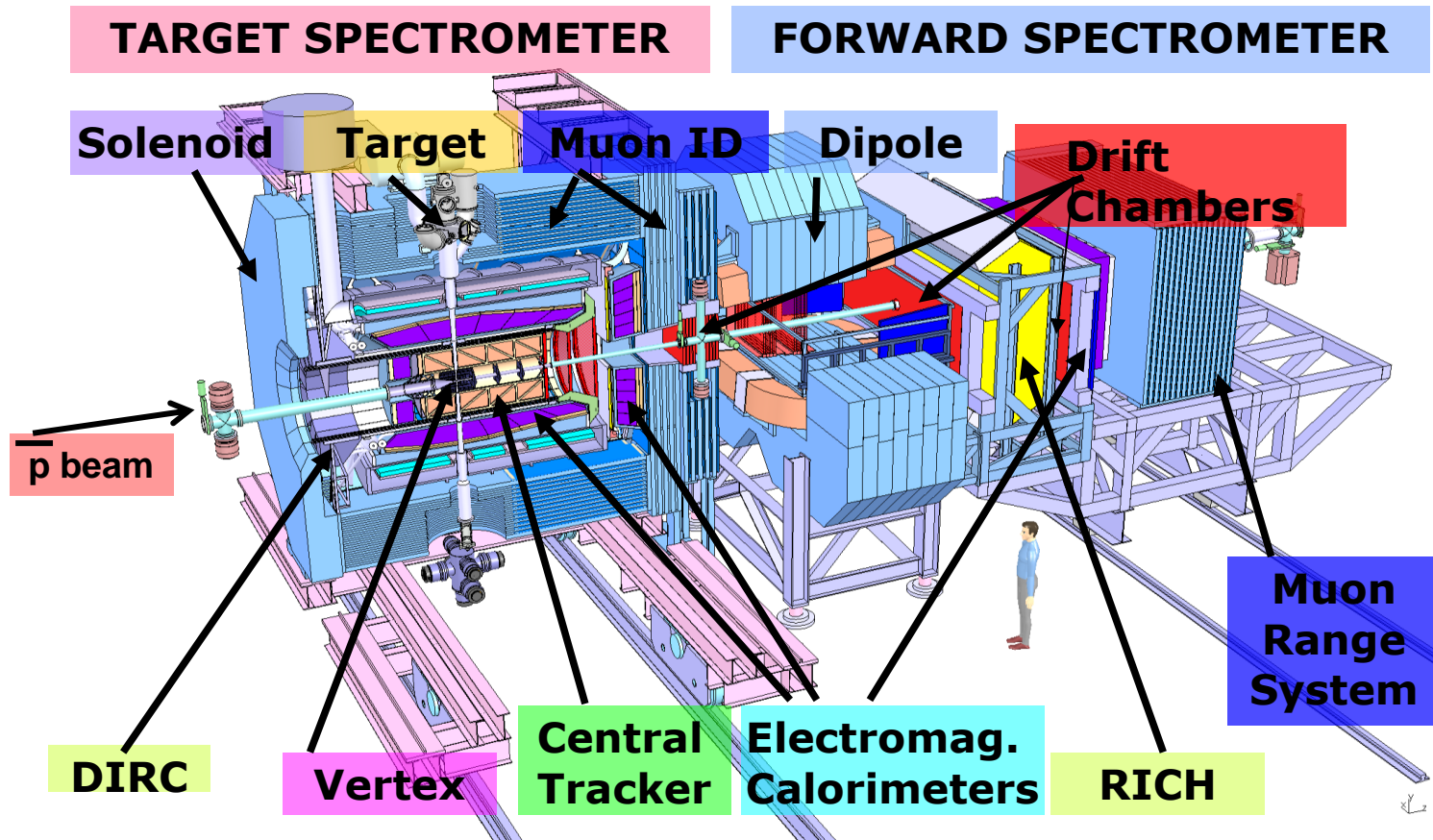
Trapezoidal (768 x 768 strips) sensors; stereo angle: 15°, pitch: 45 μm

285 μm thickness

Readout every second strip with self trigger ASIC and ToT technique for dE/dx

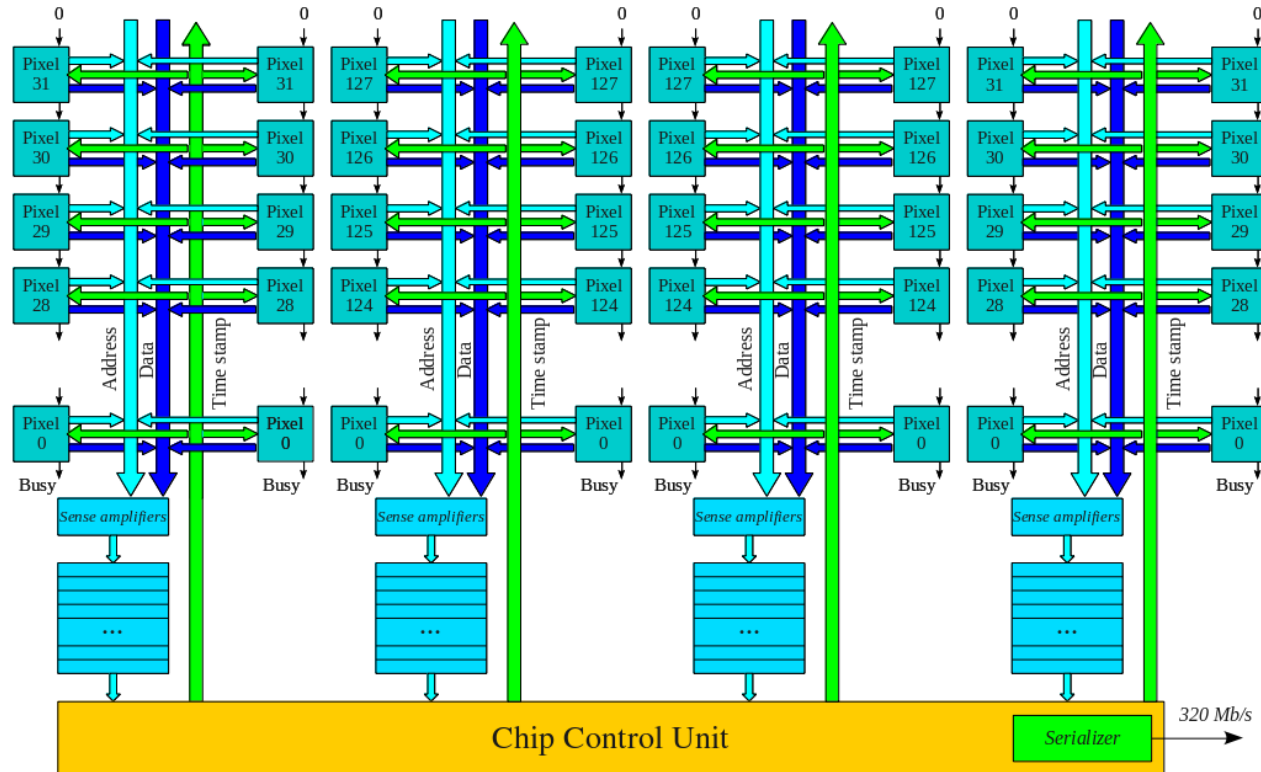
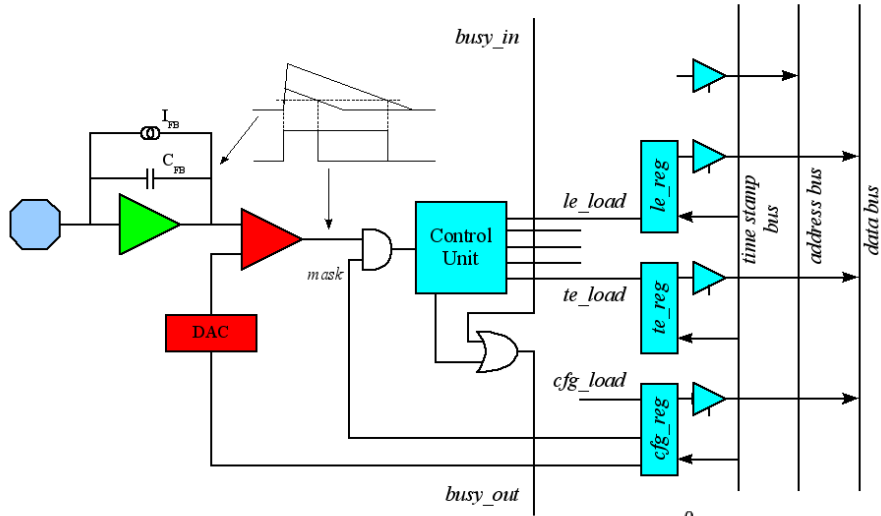


The PANDA experiment

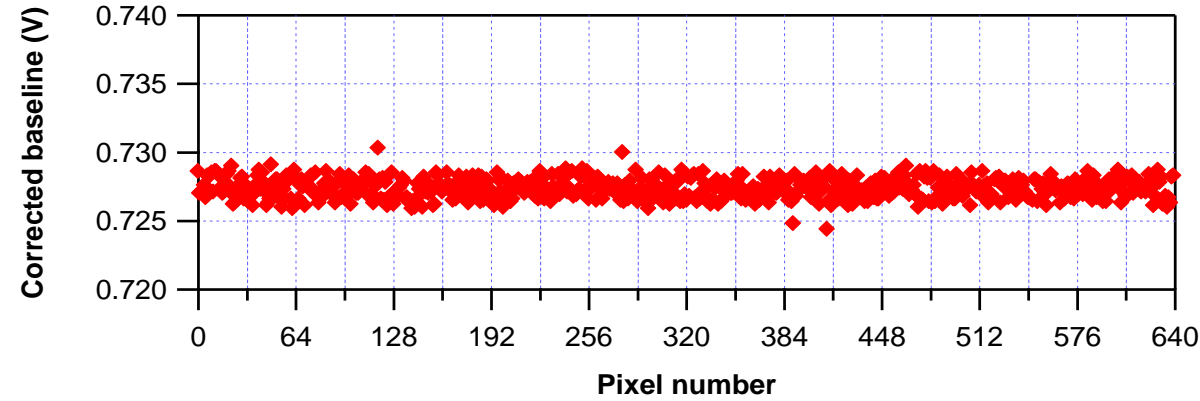


PANDA is a fixed target experiment with frozen hydrogen pellet and heavier nuclear targets (N, Ne, Ar...)

ToPix

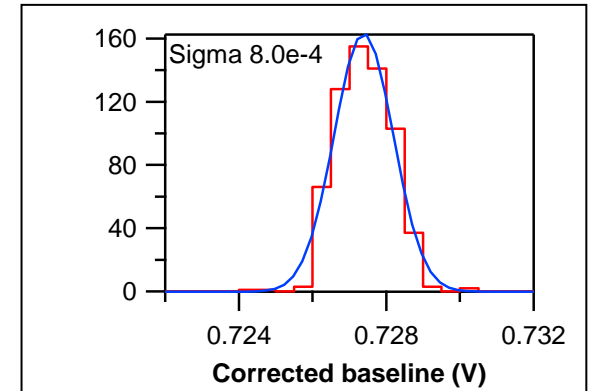


ToPix_v4

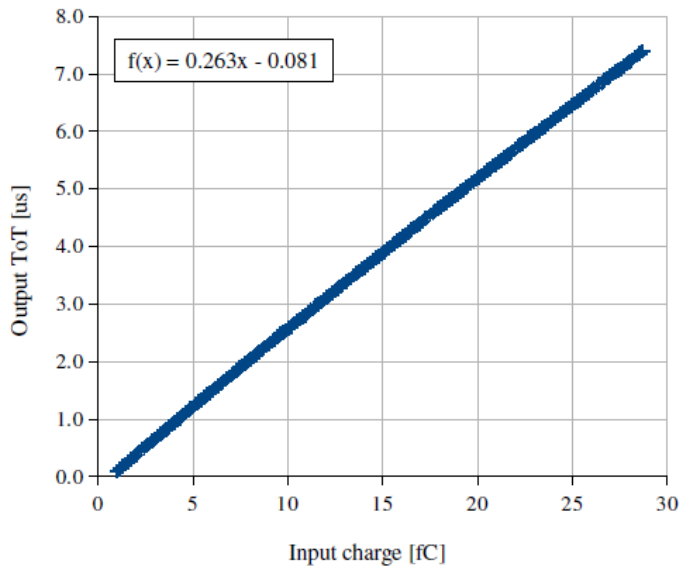


Measured performance @ 160 MHz clock

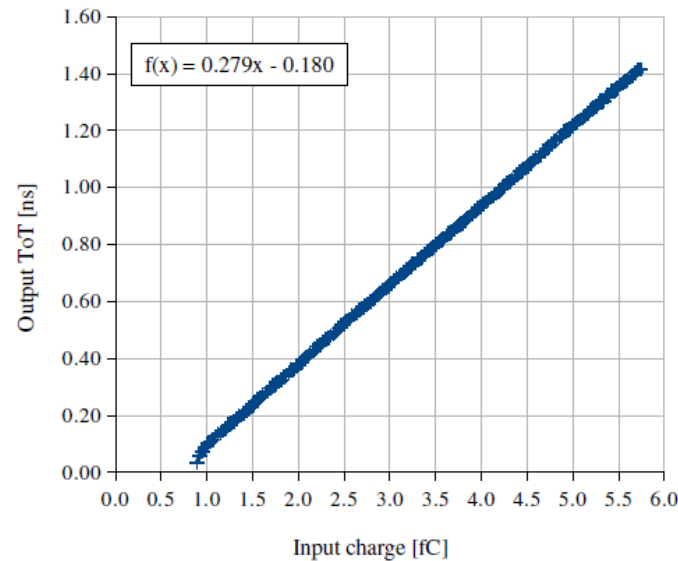
640 pixel DACs completely linear
Easy calibration



Full range

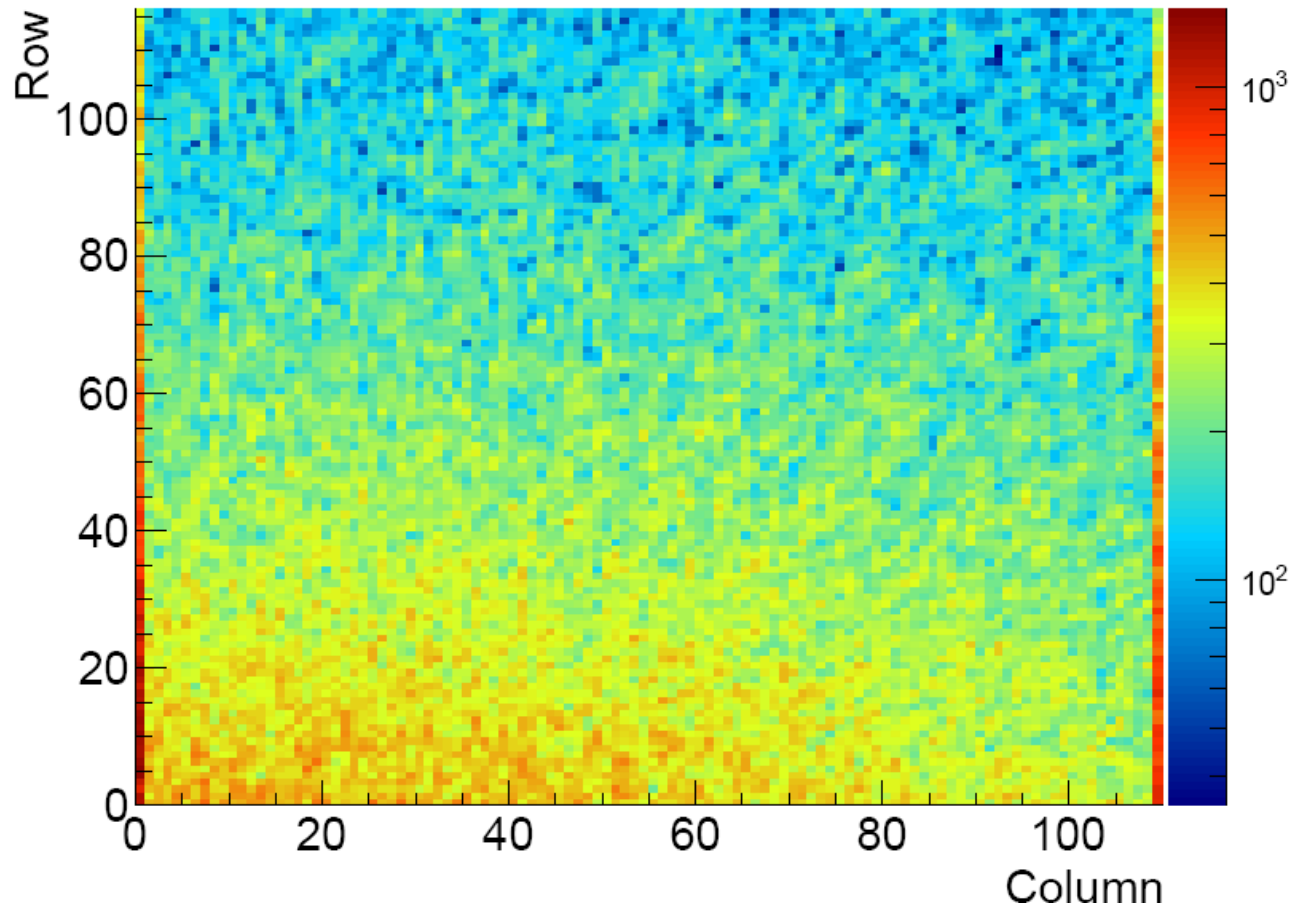


Range 0÷6 fC



Hit map from simulation

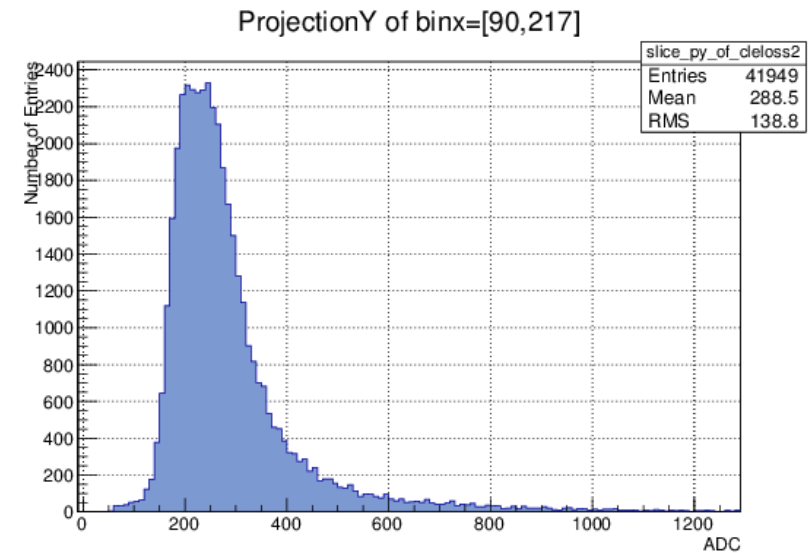
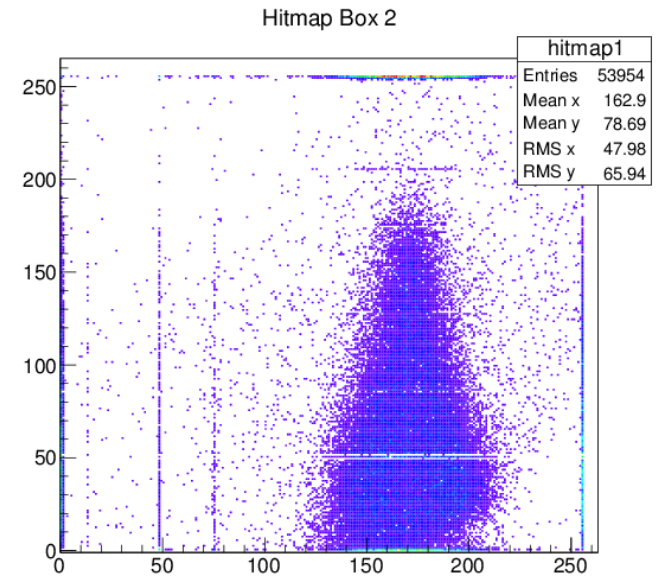
Hits / s - 116 Rows 110 Columns



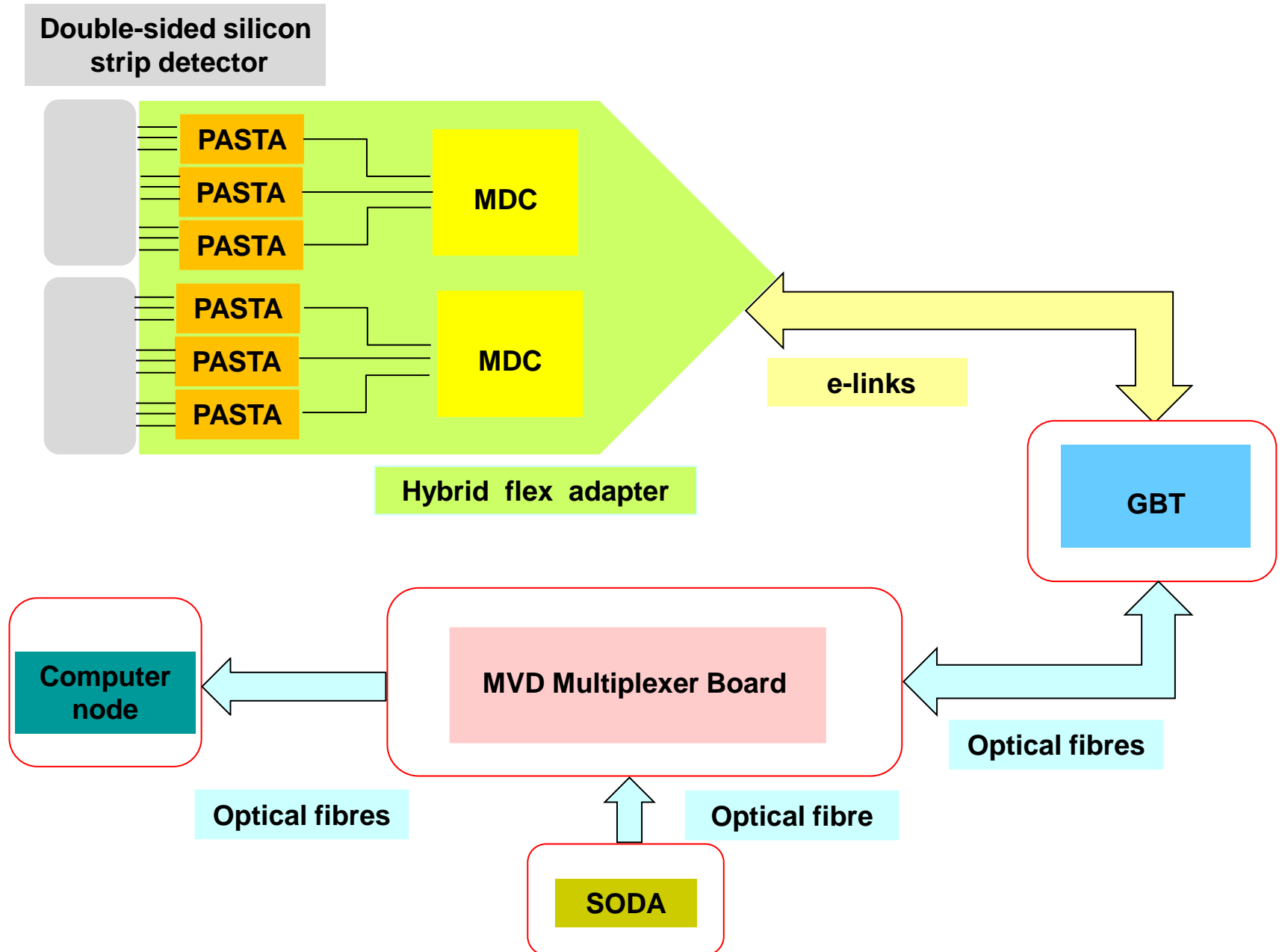
Strip prototypes



- ❑ Flex-PCB and 3.5 cm x 3.5 cm PANDA fullsize sensor (+APV25 chips)
- ❑ Trapezoidal sensors



Strip readout architecture



Pixel readout architecture

